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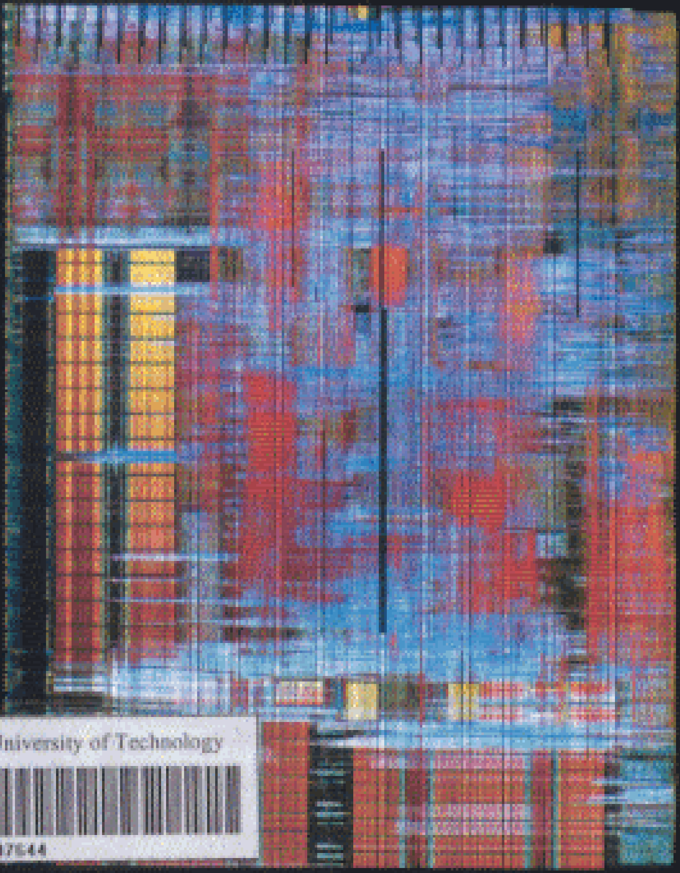
SOLID STATE ELECTRONIC DEVICES



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